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NCE P-Channel Enhancement Mode Power MOSFET

Description

The NCE20P09S uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a load switch or in PWM applications.

General Features

• $V_{DS} = -20V, I_{D} = -9A$

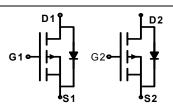
 $R_{DS(ON)}$ < 28m Ω @ V_{GS} =-4.5V

 $R_{DS(ON)}$ < 40m Ω @ V_{GS} =-2.5V

- High power and current handing capability
- Lead free product is acquired
- Surface Mount Package

Application

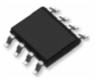
- Motor drive
- Load switch
- Power management



Schematic diagram



Marking and pin assignment



SOP-8 top view

Package Marking And Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE20P09	NCE20P09S	SOP-8	Ø330mm	12mm	2500 units

Absolute Maximum Ratings (T_A=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	-20	V
Gate-Source Voltage	Vgs	±12	V
Drain Current-Continuous	I _D	-9	Α
Drain Current-Pulsed (Note 1)	I _{DM}	-40	Α
Maximum Power Dissipation	P _D	3.1	W
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	-55 To 150	$^{\circ}$

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	R _{θJA}	42	°C/W
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Electrical Characteristics (T_A=25°Cunless otherwise noted)

Parameter S		Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V_{GS} =0 V I_D =-250 μ A	-20	-	-	V



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Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-20V,V _{GS} =0V	-	-	-1	μΑ
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±12V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	V _{DS} =V _{GS} ,I _D =-250μA	-0.5	-0.7	-1.4	V
Drain-Source On-State Resistance	Б	V _{GS} =-4.5V, I _D =-6A	-	22	28	mΩ
Diain-Source On-State Resistance	$R_{DS(ON)}$	V _{GS} =-2.5V, I _D =-5A		32	40	mΩ
Forward Transconductance	g FS	V _{DS} =-15V,I _D =-6A	-	17	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{lss}	V _{DS} =-10V,V _{GS} =0V,	-	2100	-	PF
Output Capacitance	Coss	, 55	-	498	-	PF
Reverse Transfer Capacitance	C _{rss}	F=1.0MHz - 300 -		-	PF	
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}		-	25	-	nS
Turn-on Rise Time	t _r	V_{DD} =-10V, R_L =10 Ω ,	-	30	-	nS
Turn-Off Delay Time	$t_{d(off)}$	V_{GS} =-4.5 V , R_{GEN} =6 Ω	-	70	-	nS
Turn-Off Fall Time	t _f		-	50	-	nS
Total Gate Charge	Qg		-	17	-	nC
Gate-Source Charge	Q _{gs}	V _{DS} =-10V,I _D =-6A,V _{GS} =-4.5V	-	4.1	-	nC
Gate-Drain Charge	Q_{gd}		-	4.3	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =-9A	-	-	-1.2	V

Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to production



Typical Electrical and Thermal Characteristics

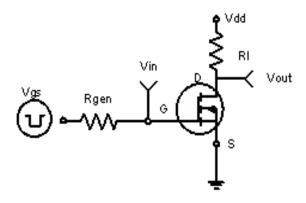


Figure 1 Switching Test Circuit

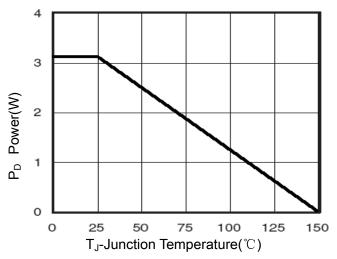


Figure 3 Power Dissipation

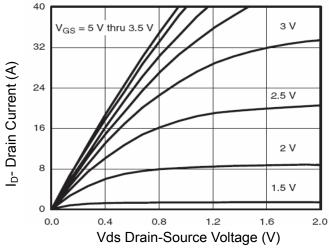


Figure 5 Output Characteristics

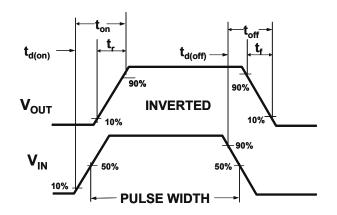


Figure 2 Switching Waveforms

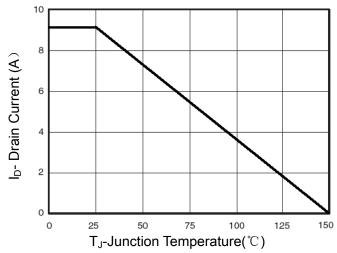


Figure 4 Drain Current

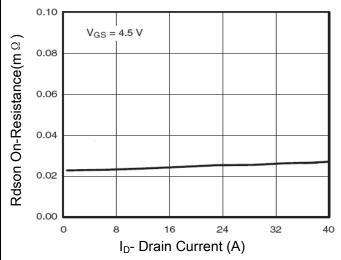


Figure 6 Drain-Source On-Resistance



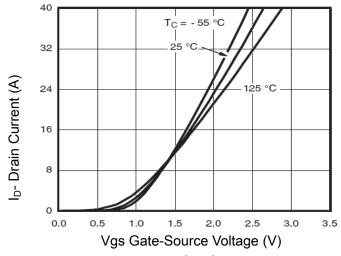


Figure 7 Transfer Characteristics

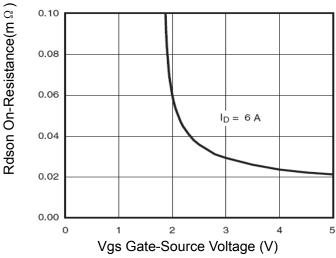
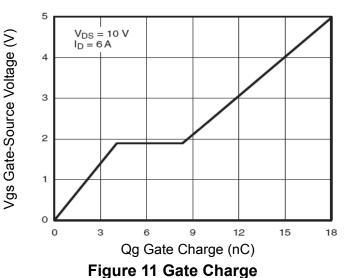


Figure 9 Rdson vs Vgs



1.6 V_{GS} = 4.5 V I_D = 6 A

1.2

1.2

0.8

0.6

-50 -25 0 25 50 75 100 125 150

T_J-Junction Temperature(°C)

Figure 8 Drain-Source On-Resistance

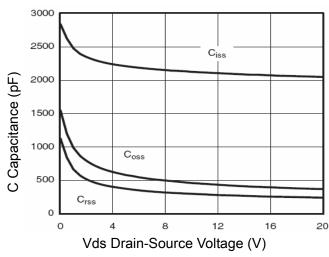


Figure 10 Capacitance vs Vds

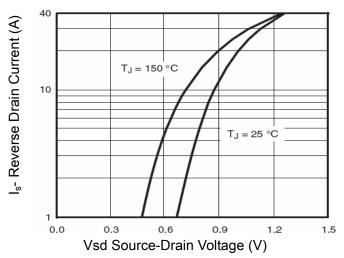


Figure 12 Source- Drain Diode Forward



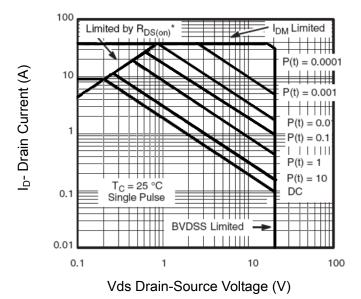


Figure 13 Safe Operation Area

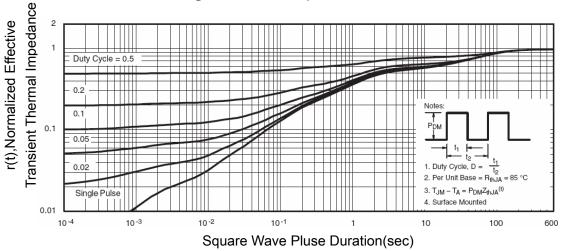
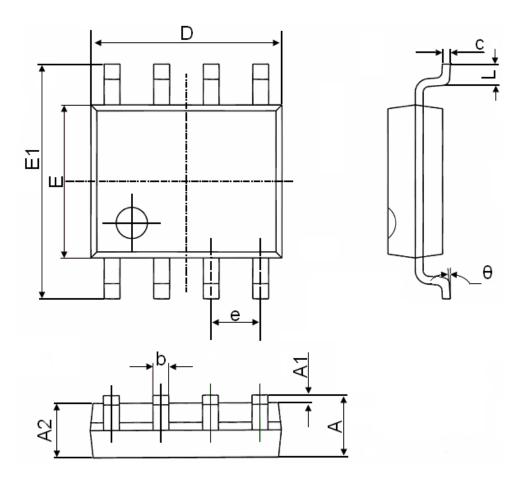


Figure 14 Normalized Maximum Transient Thermal Impedance

Pb Free Product

SOP-8 Package Information



Complete I	Dimensions In	Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
А	1.350	1.750	0.053	0.069	
A1	0.100	0.250	0.004	0.010	
A2	1.350	1.550	0.053	0.061	
b	0.330	0.510	0.013	0.020	
С	0.170	0.250	0.006	0.010	
D	4.700	5.100	0.185	0.200	
E	3.800	4.000	0.150	0.157	
E1	5.800	6.200	0.228	0.244	
е	1.270(BSC)		0.050(B	ISC)	
L	0.400	1.270	0.016	0.050	
θ	0°	8°	0°	8°	



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NCE20P09S

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